

2T935A, 2TK142**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Heavy output current. Small saturation voltage drop. Good output character.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, low frequency power amplify, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	
			2T935A	2TK142
Collector-Emitter Voltage	V _{CEO}	V	80	200
Emitter-Base Voltage	V _{EBO}	V	5	5
Max. Collector Current	I _{CM}	A	20	60
Max. Collector Dissipation (T _c =75°C)	P _{CM}	W	40	250
Junction Temperature	T _{jm}	°C	175	175
Storage Temperature	T _{stg}	°C	-55~+175	-55~+175
Emitter-Base Leakage Current	I _{EBO}	mA	-	-
			-	-
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:3.0	Max.:5.0
			V _{CE} =80V	V _{CE} =200V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:1.0	Max.:1.0
			I _c =15A, I _B =3A	I _c =30A, I _B =4.8A
DC Current Gain	h _{FE}		Min.:20, Max.:100	Min.:15, Max.:100
			V _{CE} = 5V, I _c =15A	V _{CE} = 5V, I _c =30A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	80	200
			I _c =1mA	I _c =1mA
E-Base Breakdown Voltage	V _{(BR)EBO}	V	5	5
			I _E =5mA	I _E =350mA

Outline and Dimensions: